

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	9984	semiconductor and cmos and (gate adj electrode)	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM; TDB	2002/01/15 16:45
2	BRS	L2	1556	1 and (tantalum or ta or (tantalum adj nitride) or tan or (molybdenum adj silicide) or mosi or (molybdenum adj nitride) or mon)	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM; TDB	2002/01/15 16:48
3	BRS	L3	18	1 and (tantalum or ta) and ((tantalum adj nitride) or tan) and ((molybdenum adj silicide) or mosi) and ((molybdenum adj nitride) or mon)	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM; TDB	2002/01/15 16:50

	Comments	Error Definition	Errors
1			0
2			0
3			0